



PRELIMINARY

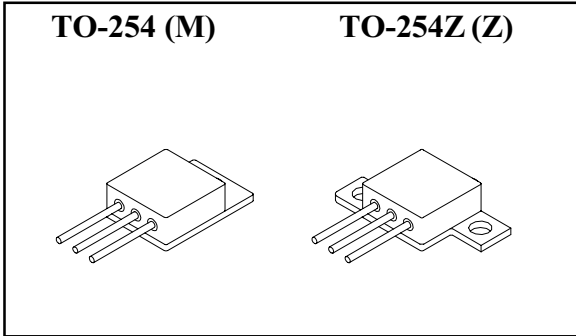
SOLID STATE DEVICES, INC.

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DESIGNER'S DATA SHEET

SFF50N20M
SFF50N20Z

50 AMPS
200 VOLTS
0.055 Ω
N-CHANNEL
POWER MOSFET

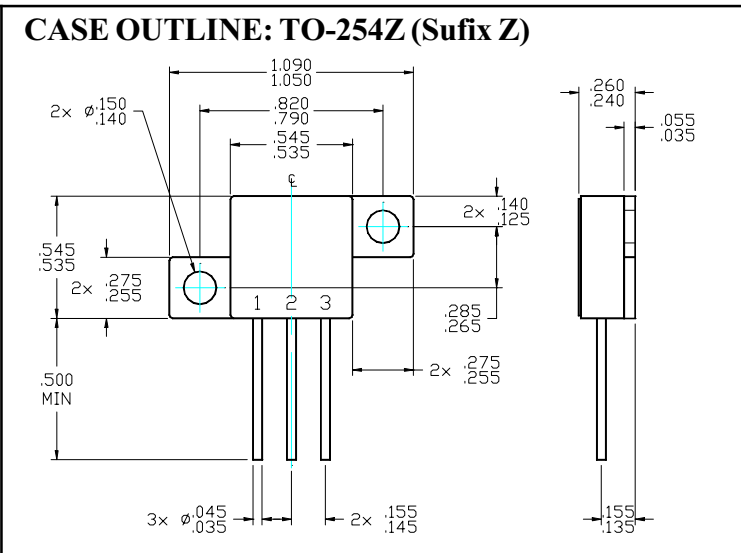
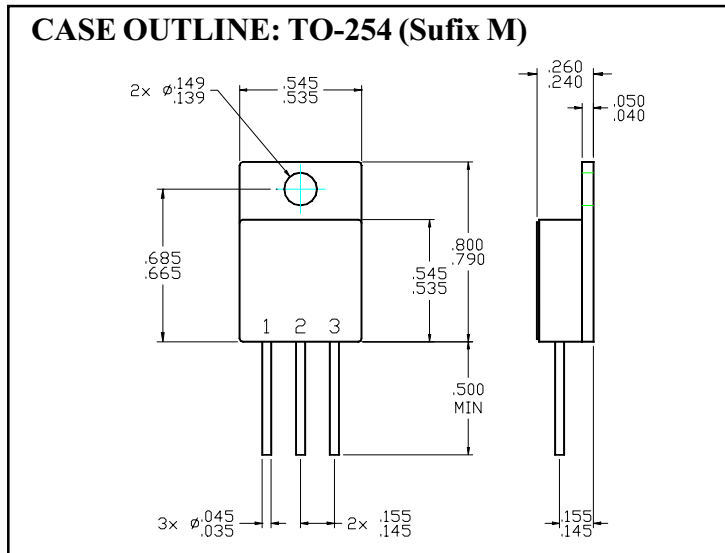


- FEATURES:**
- Rugged construction with polysilicon gate
 - Low RDS (on) and high transconductance
 - Excellent high temperature stability
 - Very fast switching speed
 - Fast recovery and superior dv/dt performance
 - Increased reverse energy capability
 - Low input and transfer capacitance for easy paralleling
 - Hermetically sealed package
 - TX, TXV, and Space Level screening available
 - Replaces: IXTH50N20 Types

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	50	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.83	°C/W
Total Device Dissipation	P _D	150 114	Watts

@ TC = 25°C
@ TC = 55°C



NOTE: All specifications are subject to change without notification. SCDs for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00129E

